



# 600V, 40A, Trench FS II Fast IGBT

### General Description:

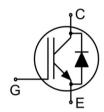
Using MJ's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

#### **Features**

- ◆ Trench FSII Technology offering
- ♦ Very low VcE (sat)
- High speed switching
- ◆ Positive temperature coefficient in V<sub>CE</sub> (sat)
- ◆ Very tight parameter distribution
- ◆ High ruggedness, temperature stable behavior

# **Application**

- ◆ Air Condition
- Inverters
- Motor drives







TO-3P

### Package Marking and Ordering Information

Device	Device Package	Device Marking
MJ40TH60BP	TO-3P	MJ40TH60BP

#### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Value	Units
Collector-Emitter Voltage	Vces	600	V
Gate- Emitter Voltage	VGES	±30	V
Collector Current	Ic	80	А
Collector Current @Tc = 100 °C	Ic	40	А
Pulsed Collector Current, tp limited by T <sub>jmax</sub>	Cplus	120	А
turn off safe operating area, VcE=600V, Tj=150°C	-	120	А
Diode Continuous Forward Current @Tc = 100 °C	lF	30	А
Diode Maximum Forward Current	IFM	90	А
Power Dissipation @ Tc = 25°C	Po	286	W
Power Dissipation @Tc = 100 °C	Po	143	W
Operating Junction and Storage Temperature Range	TJ,Tstg	-55 to +175	°C
Maximum Temperature for Soldering	T∟	260	°C
Short circuit withstand time V <sub>SE</sub> =15.0V, V <sub>CC</sub> ≤400V, Allowed number of short circuits<1000Time between short circuits:≥1.0s,Tj≤150°C	tsc	5	us





### Thermal Characteristic

Parameter	Symbol	Value	Units
Thermal Resistance, Junction to case for IGBT	Rejc	0.52	°C/W
Thermal Resistance, Junction to case for Diode	Rejc	2.12	°C/W
Thermal Resistance, Junction to Ambient	Reja	40	°C/W

### Electrical Characteristics (Tc=25°C unless otherwise noted)

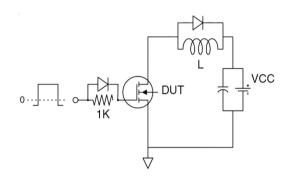
Doromotor	Cymhol			Value			Units
Parameter	Parameter Symbol Test Condi		naitions	Min	Тур	Max	Units
Static Characteristics							
Collector-Emitter Breakdown Voltage	V(BR)CES	V <sub>GE</sub> =0V,	Ice=1mA	600	-	-	V
Collector-Emitter Leakage Current	Ices	V <sub>GE</sub> =0V,\	/ce=600V	-	-	4	μA
Gate to Emitter Forward Leakage	IGES(F)	V <sub>GE</sub> =+30	V,VcE=0V	-	-	200	nA
Gate to Source Reverse Leakage	IGES(R)	V <sub>GE</sub> =-30	V,VcE=0V	-	-	200	nA
Collector-Emitter Saturation Voltage	VcE(sat)	Ic=40A	Tj=25°C	-	1.7	1.9	V
Collector-Efficiel Saturation voltage	V CE(sat)	V <sub>GE</sub> =15V	Tj=150°C	-	1.9	_	V
Gate Threshold Voltage	V <sub>GE(th)</sub>	Ic=1mA	V <sub>CE</sub> =V <sub>GE</sub>	4.0	5.0	6.0	V
Dynamic Characteristics							
Input Capacitance	Cies	Vce=25V,Vge=0V, f=1MHz		-	4894	-	pF
Output Capacitance	Coss			-	136	-	pF
Reverse Transfer Capacitance	Crss			-	94	-	pF
Total Gate Charge	Qg	Vcc=480V, Ic=40A VeE=15V VeE=15V,Vcc≤400V, tsc≤5us,Tj≤150°C		-	176	-	nC
Gate to Emitter Charge	Qge			-	38	-	nC
Gate to Collector Charge	Qgc			-	73	-	nC
Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	Ic(sc)			-	250	-	А
Switching Characteristics							
Turn-on Delay Time	t <sub>d</sub> (ON)			-	19	-	ns
Rise Time	tr			-	17	-	ns
Turn-Off Delay Time	t <sub>d(OFF)</sub>	Vce=400V,lc=40A Vce=0/15V, R <sub>g</sub> =5Ω Inductive Load		-	168	-	ns
Fall Time	tr			-	16	-	ns
Turn-On Switching Loss	Eon			-	0.58	-	mJ
Turn-Off Switching Loss	Eoff			-	0.48	-	mJ
Turn-Off Switching Loss	Ets			_	1.06	-	mJ



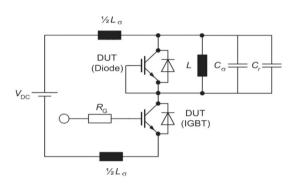
## Electrical Characteristics of the Diode (Tc= 25°C unless otherwise specified):

Doromotor	Symbol	Test Conditions	Rating			l lm:to
Parameter	Symbol	rest Conditions	Min	Тур	Max	Units
Diode Forward Voltage	VFM	I=30A	-	1.65	2.0	V
Reverse Recovery Time	Tm		_	170	_	ns
Diode Peak Reverse Recovery Current	IRRM	I <sub>F</sub> =30A,di/dt=200A/uS	-	6.5	-	А
Reverse Transfer Capacitance	Qrr		_	0.7	-	uC
Pulse width ttp≤380μs,δ≤2%						

#### **Test Circuit**

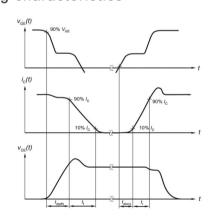


Gate Charge Test Circuit

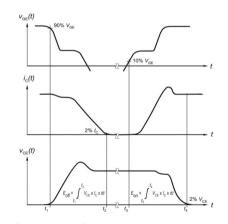


Switch Time Test Circuit

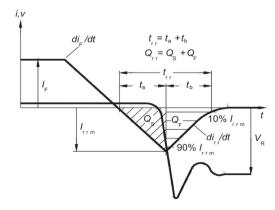
### Switching characteristics



definition of switching times



definition of switching losses

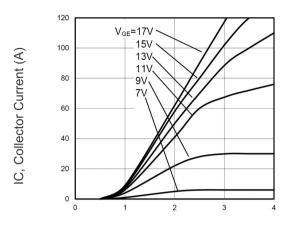


Definition of diode switching characteristics

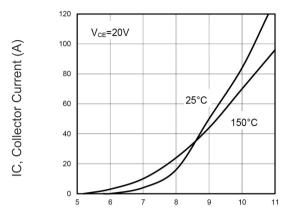




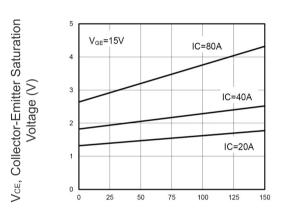
### Typical Electrical and Thermal Characteristics



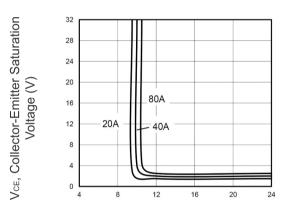
Vce, Collector-Emitter Voltage (V)
Figure 1 Output Characteristics



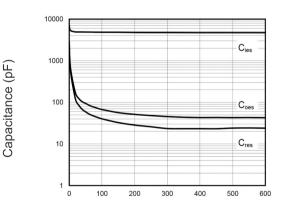
V<sub>GE</sub>, Gate-Emitter Voltage (V)
Figure 2 Transfer Characteristics



TJ, Junction Temperature (°C)
Figure 3 V<sub>CEsat</sub> vs. Case Temperature

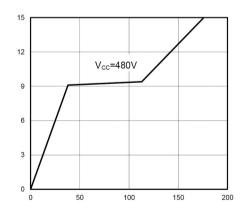


VGE, Gate-Emitter Voltage (V)
Figure 4 Saturation Voltage vs. VGE



Vce, Collector-Emitter Voltage (V)

Figure 5 Capacitance Characteristics



QG, Total Gate Charge (nC)
Figure 6 Gate charge waveform

VGE, Gate-Emitter Voltage (V)

#### Typical Electrical and Thermal Characteristics

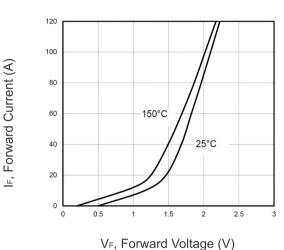


Figure 7 Forward Characteristics

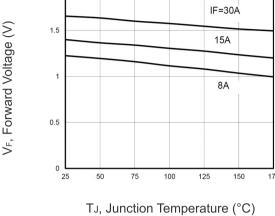
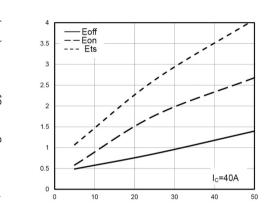


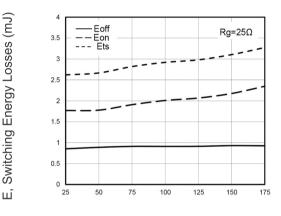
Figure 8 VF vs. Temperature



E, Switching Energy Losses (mJ)

Figure 9 Typical Switching Times as a Function of Gate Resistor

R<sub>G</sub>, Gate Resistor (Ω)



TJ, Junction Temperature (°C)
Figure 10 Typical Switching Times as a
Function of Junction Temperature

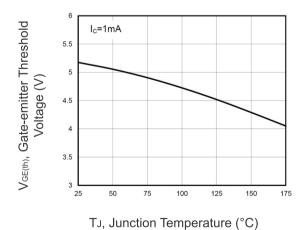


Figure 11 Gate-emitter Threshold Voltage as a Function of Junction Temperature

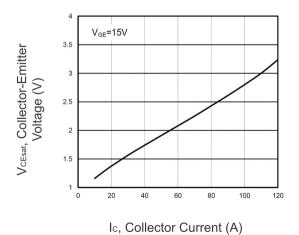
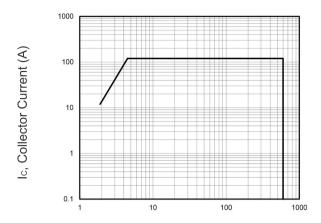


Figure 12 Typical Collector-emitter Saturation Voltage as a function of Collector Current



### Typical Electrical and Thermal Characteristics



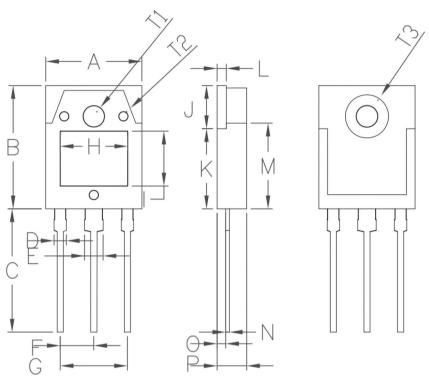
Vce, Collector-Emitter Voltage (V)

Figure 13 Forward Bias Safe Operating Area





## TO-3P-3L Package Information



Symph al	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	15.50	15.70	0.61	0.62	
В	19.70	20.10	0.78	0.79	
С	20.10	20.50	0.79	0.81	
D	2	2.00	0.0	08	
E	3	3.00	0.	12	
F	5	5.45	0.:	21	
G	10	0.90	0.4	43	
Н	10.80	11.00	0.43	0.43	
I	8.80	9.00	0.35	0.35	
J	6.85	7.15	0.27	0.28	
K	12.75	13.05	0.50	0.51	
L	1.49	1.51	0.06	0.06	
M	13.70	14.00	0.54	0.55	
N	0.59	0.61	0.02	0.02	
0	1.32	1.48	0.05	0.06	
Р	4.70	4.90	0.19	0.19	
S		4°		16°	
T1	3	3.50		14	
T2	1	1.50 0.06		06	
Т3	7	7.00	0.28		





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